优尚

YOUSHANG SEMICONDUCTOR

设计研发新型功率器件

各类小信号开关

中低压及高压大电流等场效应管

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Product Summary

BV_{DSS}	$R_{DS(ON)\ MAX}$	$I_{D\ MAX}$ T_C = +25°C
-30V	25mΩ @ V_{GS} = -10V	-27A
	38mΩ @ V_{GS} = -4.5V	-22A

Features

- 100% Unclamped Inductive Switch (UIS) Test In Production
- Low On-Resistance
- Fast Switching Speed

Description and Applications

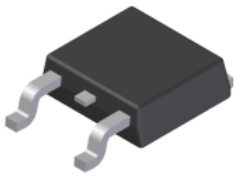
This MOSFET is designed to meet the stringent requirements of Automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

- Backlighting
- DC-DC Converters
- Power Management Functions

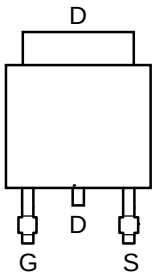
Mechanical Data

- Case: TO252 (DPAK)
- Case Material: Molded Plastic, “Green” Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 e3
- Weight: 0.33 grams (Approximate)

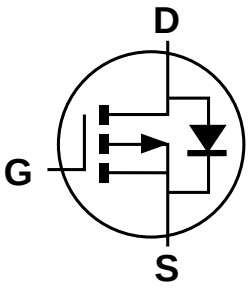
TO252 (DPAK)



Top View



Top View
Pin-Out



Equivalent Circuit

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V_{DSS}	-30	V
Gate-Source Voltage			V_{GSS}	±20	V
Continuous Drain Current (Note 7) V_{GS} = -10V	Steady State	T_C = +25°C T_C = +70°C	I_D	-27 -22	A
	t<10s	T_A = +25°C T_A = +70°C	I_D	-11 -8.6	A
Maximum Body Diode Continuous Current			I_S	-2.5	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			I_{DM}	-40	A
Avalanche Current (Note 8) L = 0.1mH			I_{AS}	-22	A
Avalanche Energy (Note 8) L = 0.1mH			E_{AS}	24	mJ

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 6)	T_A = +25°C	P_D	1.6	W
	T_A = +70°C		1.0	
Thermal Resistance, Junction to Ambient (Note 6)	Steady state	$R_{\theta JA}$	77	°C/W
	t<10s		34	
Total Power Dissipation (Note 7)	T_A = +25°C	P_D	2.8	W
	T_A = +70°C		1.8	
Thermal Resistance, Junction to Ambient (Note 7)	Steady state	$R_{\theta JA}$	45	°C/W
	t<10s		29	
Thermal Resistance, Junction to Case (Note 7)		$R_{\theta JC}$	4.5	
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 9)						
Drain-Source Breakdown Voltage	BV_{DSS}	-30	—	—	V	V_{GS} = 0V, I_D = -250µA
Zero Gate Voltage Drain Current T_J = +25°C	I_{DSS}	—	—	-1	µA	V_{DS} = -30V, V_{GS} = 0V
Gate-Source Leakage	I_{GSS}	—	—	±100	nA	V_{GS} = ±20V, V_{DS} = 0V
ON CHARACTERISTICS (Note 9)						
Gate Threshold Voltage	$V_{GS(TH)}$	-1	—	-2.4	V	V_{DS} = V_{GS}, I_D = -250µA
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	20	25	mΩ	V_{GS} = -10V, I_D = -7A
			29	38		V_{GS} = -4.5V, I_D = -6.2A
Diode Forward Voltage	V_{SD}	—	-0.7	-1.2	V	V_{GS} = 0V, I_S = -2.1A
DYNAMIC CHARACTERISTICS (Note 10)						
Input Capacitance	C_{iss}	—	1241	—	pF	V_{DS} = -15V, V_{GS} = 0V f = 1.0MHz
Output Capacitance	C_{oss}	—	147	—	pF	
Reverse Transfer Capacitance	C_{rss}	—	110	—	pF	
Gate Resistance	R_G	—	15	—	Ω	V_{DS} = 0V, V_{GS} = 0V, f = 1MHz
Total Gate Charge (V_{GS} = -10V)	Q_g	—	22	—	nC	V_{DS} = -15V, I_D = -7A
Total Gate Charge (V_{GS} = -4.5V)	Q_g	—	11	—	nC	
Gate-Source Charge	Q_{gs}	—	3.5	—	nC	
Gate-Drain Charge	Q_{gd}	—	4.7	—	nC	
Turn-On Delay Time	$t_{D(ON)}$	—	9.7	—	ns	V_{GS} = -10V, V_{DD} = -15V, R_{GEN} = 6Ω I_D = -7A
Turn-On Rise Time	t_R	—	17.1	—	ns	
Turn-Off Delay Time	$t_{D(OFF)}$	—	60.5	—	ns	
Turn-Off Fall Time	t_F	—	40.4	—	ns	

Notes: 6. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
7. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
8. I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep T_J = +25°C.
9. Short duration pulse test used to minimize self-heating effect.
10. Guaranteed by design. Not subject to product testing.

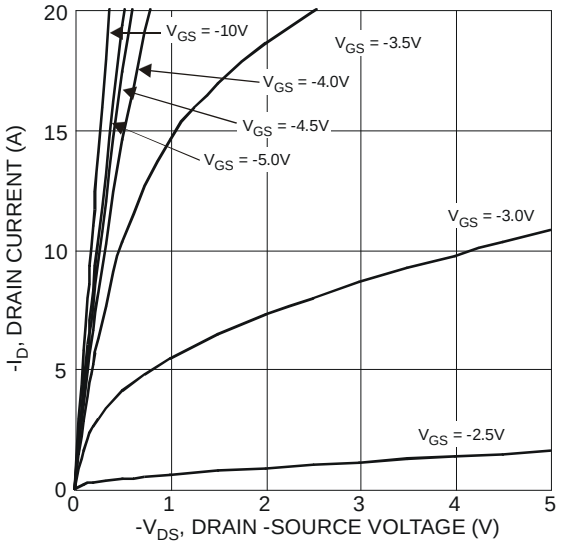


Figure 1 Typical Output Characteristics

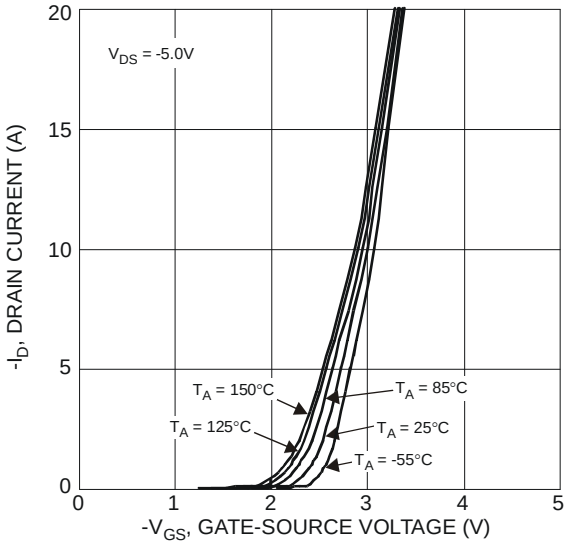


Figure 2 Typical Transfer Characteristics

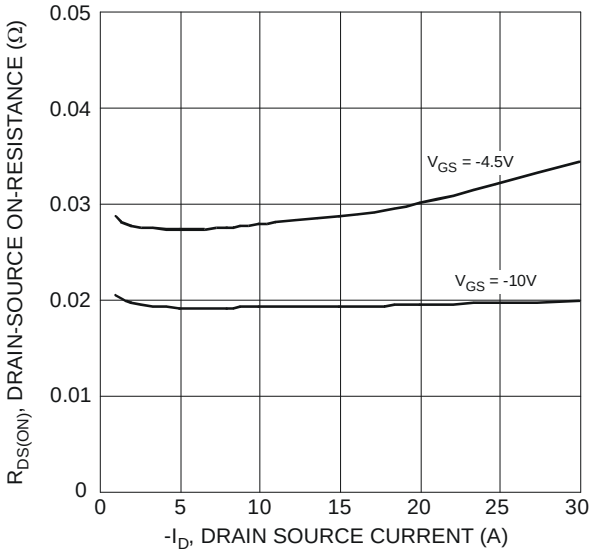


Figure 3 Typical On-Resistance vs.
Drain Current and Gate Voltage

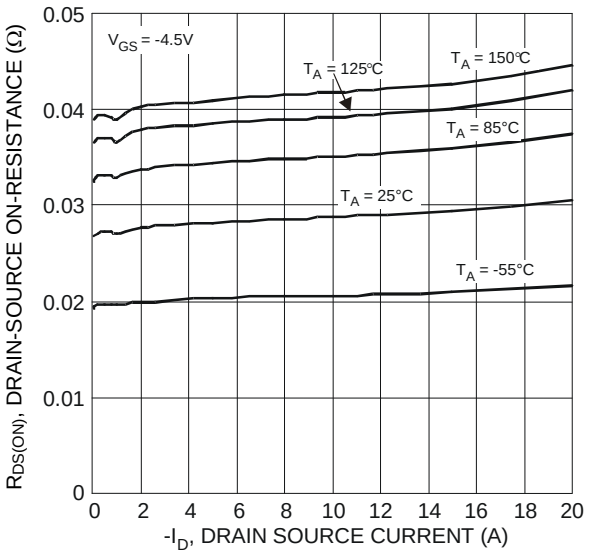


Figure 4 Typical On-Resistance vs.
Drain Current and Temperature

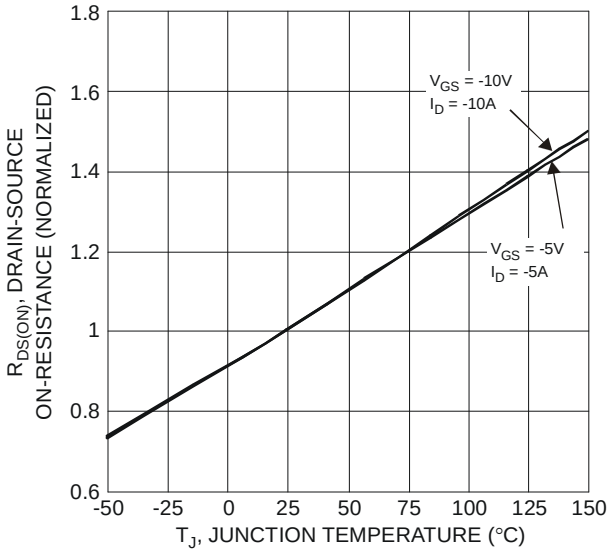


Figure 5 On-Resistance Variation with Temperature

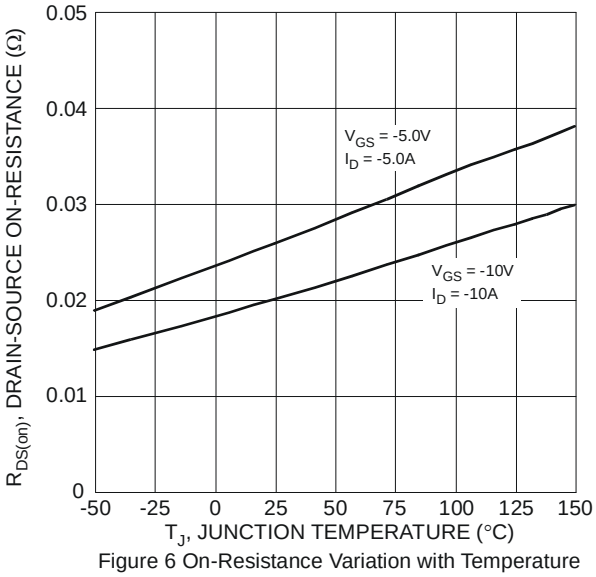


Figure 6 On-Resistance Variation with Temperature

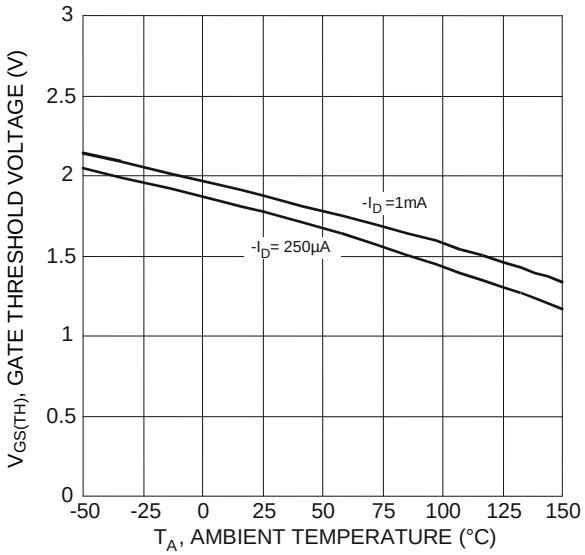


Figure 7 Gate Threshold Variation vs. Ambient Temperature

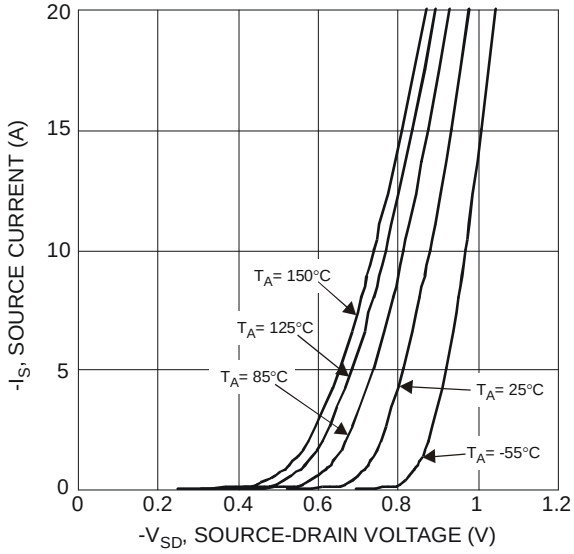


Figure 8 Diode Forward Voltage vs. Current

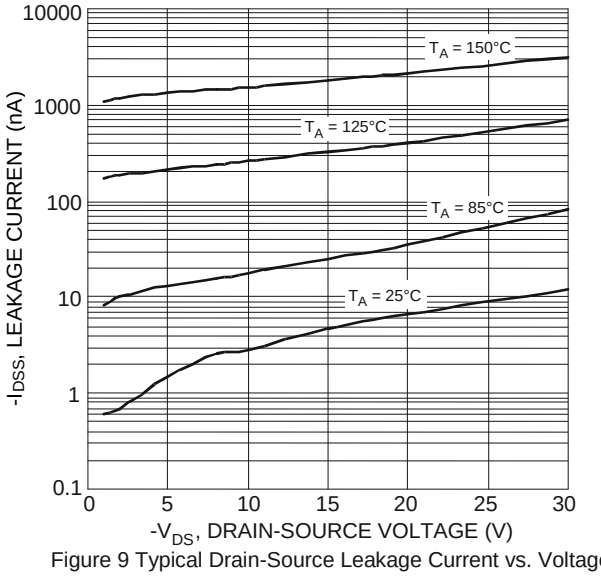


Figure 9 Typical Drain-Source Leakage Current vs. Voltage

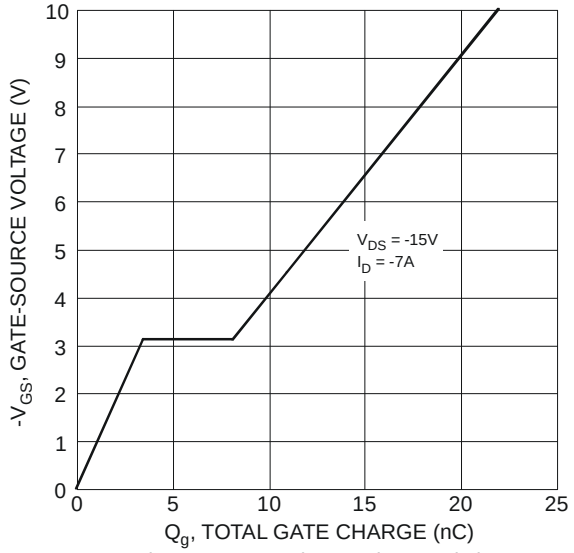


Figure 10 Gate-Charge Characteristics

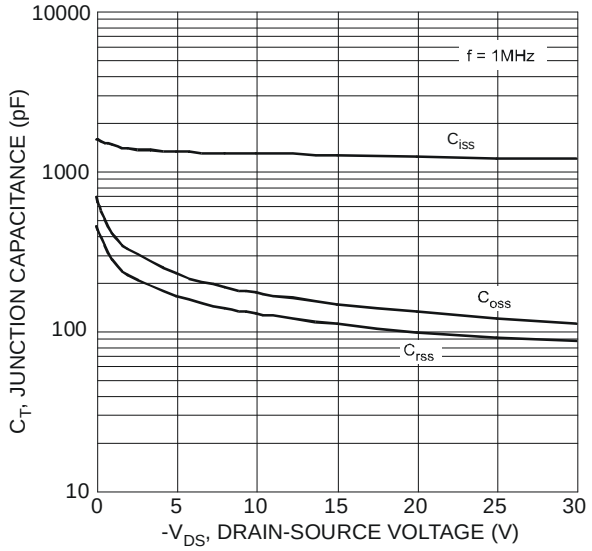


Figure 11 Typical Junction Capacitance

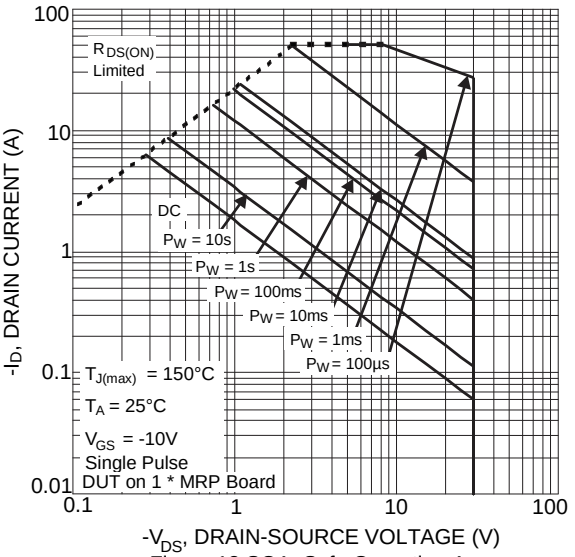


Figure 12 SOA, Safe Operation Area

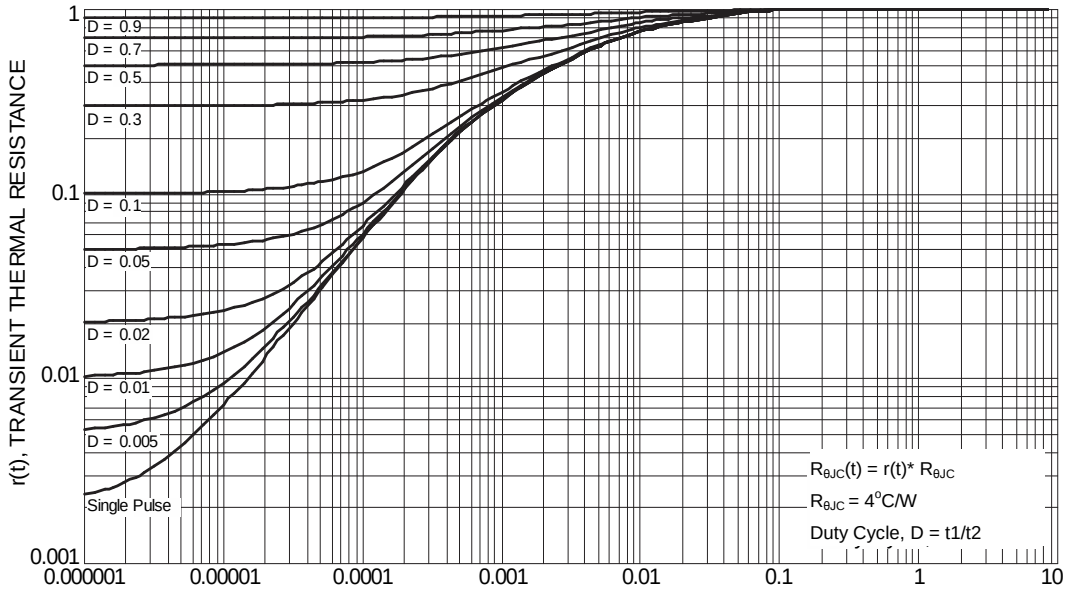
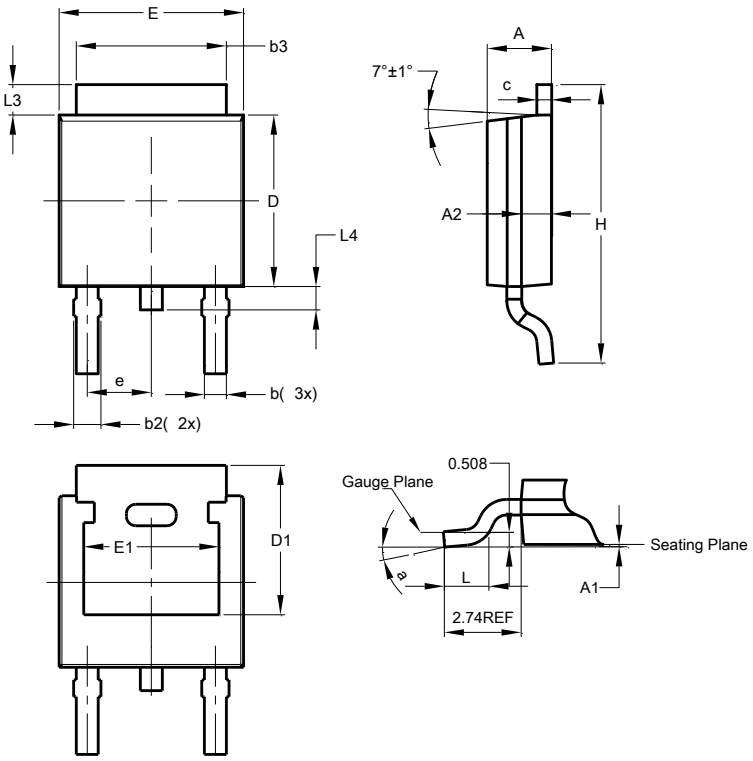


Figure 13 Transient Thermal Resistance

Package Outline Dimensions

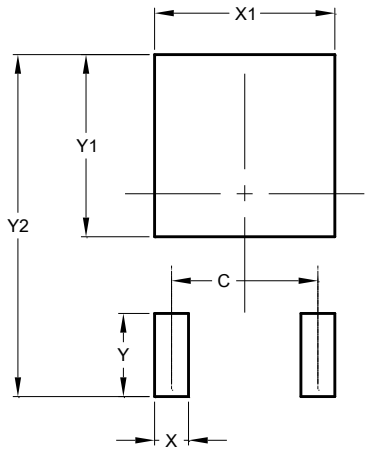
TO252 (DPAK)



TO252 (DPAK)			
Dim	**Min**	**Max**	**Typ**
A	2.19	2.39	2.29
A1	0.00	0.13	0.08
A2	0.97	1.17	1.07
b	0.64	0.88	0.783
b2	0.76	1.14	0.95
b3	5.21	5.46	5.33
c	0.45	0.58	0.531
D	6.00	6.20	6.10
D1	5.21	-	-
e	-	-	2.286
E	6.45	6.70	6.58
E1	4.32	-	-
H	9.40	10.41	9.91
L	1.40	1.78	1.59
L3	0.88	1.27	1.08
L4	0.64	1.02	0.83
a	0°	10°	-
All Dimensions in mm			

Suggested Pad Layout

TO252 (DPAK)



Dimensions	Value (in mm)
C	4.572
X	1.060
X1	5.632
Y	2.600
Y1	5.700
Y2	10.700